

Daniel Lizzit

List of Publications by Year in descending order

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42
papers

643
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706676

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721071

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all docs

42
docs citations

42
times ranked

1058
citing authors

#	ARTICLE	IF	CITATIONS
1	Limitations to Electrical Probing of Spontaneous Polarization in Ferroelectric-Dielectric Heterostructures. IEEE Journal of the Electron Devices Society, 2022, 10, 324-333.	1.2	7
2	CO adsorption, reduction and oxidation on Pb(Zr,Ti)O ₃ (001) surfaces associated with negatively charged gold nanoparticles. Catalysis Today, 2021, 366, 141-154.	2.2	4
3	Ion Implantation as an Approach for Structural Modifications and Functionalization of Ti ₃ C ₂ T _x MXenes. ACS Nano, 2021, 15, 4245-4255.	7.3	37
4	Transition metal carbides (MXenes) for efficient NiO-based inverted perovskite solar cells. Nano Energy, 2021, 82, 105771.	8.2	74
5	Spectroscopic view of ultrafast charge carrier dynamics in single- and bilayer transition metal dichalcogenide semiconductors. Journal of Electron Spectroscopy and Related Phenomena, 2021, 250, 147093.	0.8	9
6	Mixed Cation Halide Perovskite under Environmental and Physical Stress. Materials, 2021, 14, 3954.	1.3	14
7	Modeling Nanoscale III-V Channel MOSFETs with the Self-Consistent Multi-Valley/Multi-Subband Monte Carlo Approach. Electronics (Switzerland), 2021, 10, 2472.	1.8	0
8	Anisotropic strain in epitaxial single-layer molybdenum disulfide on Ag(110). Nanoscale, 2021, 13, 18789-18798.	2.8	5
9	Interfacial two-dimensional oxide enhances photocatalytic activity of graphene/titania via electronic structure modification. Carbon, 2020, 157, 350-357.	5.4	7
10	Resistance hysteresis correlated with synchrotron radiation surface studies in atomic sp ² layers of carbon synthesized on ferroelectric (001) lead zirconate titanate in an ultrahigh vacuum. RSC Advances, 2020, 10, 1522-1534.	1.7	7
11	Strong ferromagnetic coupling and tunable easy magnetization directions of Fe _x Co _{1-x} layer(s) intercalated under graphene. Applied Surface Science, 2020, 527, 146599.	3.1	5
12	Growth Mechanism and Thermal Stability of a MoS ₂ -Graphene Interface: A High-Resolution Core-Level Photoelectron Spectroscopy Study. Journal of Physical Chemistry C, 2020, 124, 20889-20897.	1.5	4
13	Compositional Phase Change of Early Transition Metal Diselenide (VSe ₂ and) Tj ETQq1 1 0.784314 rgBT /Overlock 10 Tf 50 2000497.	1.9	17
14	80% Valley Polarization of Free Carriers in Singly Oriented Single-Layer WS_2 on Au(111). Physical Review Letters, 2019, 123, 236802.	2.9	27
15	Momentum-resolved linear dichroism in bilayer MoS_2 . Physical Review B, 2019, 100, .	1.1	11
16	Layer and orbital interference effects in photoemission from transition metal dichalcogenides. Physical Review B, 2019, 100, .	1.1	11
17	Dual-Route Hydrogenation of the Graphene/Ni Interface. ACS Nano, 2019, 13, 1828-1838.	7.3	8
18	Electron-phonon coupling in single-layer MoS ₂ . Surface Science, 2019, 681, 64-69.	0.8	7

#	ARTICLE	IF	CITATIONS
19	Growth and structure of singly oriented single-layer tungsten disulfide on Au(111). Physical Review Materials, 2019, 3, .	0.9	18
20	Epitaxial growth of single-orientation high-quality MoS ₂ monolayers. 2D Materials, 2018, 5, 035012.	2.0	65
21	Photoemission investigation of oxygen intercalated epitaxial graphene on Ru(0001). Surface Science, 2018, 678, 57-64.	0.8	18
22	Spin Structure of K Valleys in Single-Layer WS ₂ on Au(111). Physical Review Letters, 2018, 121, 136402.	2.9	28
23	Novel single-layer vanadium sulphide phases. 2D Materials, 2018, 5, 045009.	2.0	48
24	Benchmarking of 3-D MOSFET Architectures: Focus on the Impact of Surface Roughness and Self-Heating. IEEE Transactions on Electron Devices, 2018, 65, 3646-3653.	1.6	10
25	New device concepts, transistor architectures and materials for high performance and energy efficient CMOS circuits in the forthcoming era of 3D integrated circuits. , 2018, , .		0
26	Improved surface-roughness scattering and mobility models for multi-gate FETs with arbitrary cross-section and biasing scheme. Journal of Applied Physics, 2017, 121, .	1.1	9
27	Surface roughness limited mobility in multi-gate FETs with arbitrary cross-section. , 2016, , .		4
28	Performance projection of III-V ultra-thin-body, FinFET, and nanowire MOSFETs for two next-generation technology nodes. , 2016, , .		29
29	An Improved Surface Roughness Scattering Model for Bulk, Thin-Body, and Quantum-Well MOSFETs. IEEE Transactions on Electron Devices, 2016, 63, 2306-2312.	1.6	20
30	Quasi-Ballistic Γ - and L-Valleys Transport in Ultrathin Body Strained (111) GaAs nMOSFETs. IEEE Transactions on Electron Devices, 2016, 63, 4685-4692.	1.6	4
31	Improved surface roughness modeling and mobility projections in thin film MOSFETs. , 2015, , . The impact of interface states on the mobility and drive current of 		2
32	State-of-the-art semi-classical Monte Carlo method for carrier transport in nanoscale transistors. , 2015, , .	0.8	17
33	State-of-the-art semi-classical Monte Carlo method for carrier transport in nanoscale transistors. , 2015, , .		2
34	A new formulation for surface roughness limited mobility in bulk and ultra-thin-body metal-oxide-semiconductor transistors. Journal of Applied Physics, 2014, 116, .	1.1	26
35	Simulation analysis of III–V n-MOSFETs: Channel materials, Fermi level pinning and biaxial strain. , 2014, , .		9
36	Performance Benchmarking and Effective Channel Length for Nanoscale InAs, $\text{In}_{0.53}\text{Ga}_{0.47}\text{As}$, and sSi n-MOSFETs. IEEE Transactions on Electron Devices, 2014, 61, 2027-2034.	1.6	39

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37	The impact of interface states on the mobility and the drive current of III-V MOSFETs. , 2014, , .		2
38	Surface roughness limited mobility modeling in ultra-thin SOI and quantum well III-V MOSFETs. , 2013, , .		14
39	On the optimization of SiGe and III-V compound hetero-junction Tunnel FET devices. , 2013, , .		1
40	Toward computationally efficient Multi-Subband Monte Carlo simulations of nanoscale MOSFETs. , 2013, , .		3
41	Analysis of the Performance of n-Type FinFETs With Strained SiGe Channel. IEEE Transactions on Electron Devices, 2013, 60, 1884-1891.	1.6	19
42	A Multi-Subband Monte Carlo study of electron transport in strained SiGe n-type FinFETs. , 2012, , .		1